

MOSFET

OptiMOS™ Power-MOSFET, 40 V

Features

- Optimized for high performance SMPS, e.g. sync. rec.
- Very low on-resistance $R_{DS(on)}$ @ $V_{GS}=4.5\text{ V}$
- 100% avalanche tested
- Superior thermal resistance
- N-channel
- Qualified according to JEDEC¹⁾ for target applications
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21
- Higher solder joint reliability with enlarged source interconnection

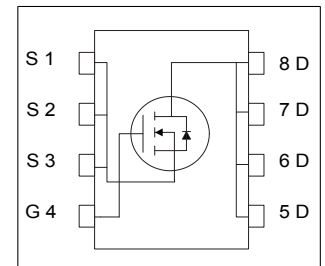


Table 1 Key Performance Parameters

| Parameter | Value | Unit |
|------------------|-------|------------|
| V_{DS} | 40 | V |
| $R_{DS(on),max}$ | 3.4 | m Ω |
| I_D | 40 | A |
| Q_{OSS} | 22 | nC |
| $Q_G(0V..10V)$ | 25 | nC |

| Type / Ordering Code | Package | Marking | Related Links |
|----------------------|----------------|---------|---------------|
| BSZ034N04LS | PG-TSDSON-8 FL | 034N04L | - |

¹⁾ J-STD20 and JESD22

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1 Maximum ratings

at $T_A=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|----------------|--------|------|------|------|---|
| | | Min. | Typ. | Max. | | |
| Continuous drain current | I_D | - | - | 40 | A | $V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=4.5\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=4.5\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=10\text{ V}$, $T_A=25\text{ °C}$, $R_{thJA}=60\text{ K/W}^1)$ |
| | | - | - | 40 | | |
| | | - | - | 40 | | |
| | | - | - | 40 | | |
| | | - | - | 19 | | |
| Pulsed drain current ²⁾ | $I_{D,pulse}$ | - | - | 160 | A | $T_C=25\text{ °C}$ |
| Avalanche energy, single pulse ³⁾ | E_{AS} | - | - | 70 | mJ | $I_D=20\text{ A}$, $R_{GS}=25\text{ }\Omega$ |
| Gate source voltage | V_{GS} | -20 | - | 20 | V | - |
| Power dissipation | P_{tot} | - | - | 52 | W | $T_C=25\text{ °C}$ $T_A=25\text{ °C}$, $R_{thJA}=60\text{ K/W}^1)$ |
| | | - | - | 2.1 | | |
| Operating and storage temperature | T_j, T_{stg} | -55 | - | 150 | °C | IEC climatic category; DIN IEC 68-1: 55/150/56 |

2 Thermal characteristics

Table 3 Thermal characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|------------|--------|------|------|------|-----------------------|
| | | Min. | Typ. | Max. | | |
| Thermal resistance, junction - case | R_{thJC} | - | 1.4 | 2.4 | K/W | - |
| Device on PCB, 6 cm ² cooling area ¹⁾ | R_{thJA} | - | - | 60 | K/W | - |

¹⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

²⁾ See Diagram 3 for more detailed information

³⁾ See Diagram 13 for more detailed information

3 Electrical characteristics

Table 4 Static characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|----------------------------------|---------------|--------|------------|------------|------------------|---|
| | | Min. | Typ. | Max. | | |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | 40 | - | - | V | $V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$ |
| Gate threshold voltage | $V_{GS(th)}$ | 1.2 | - | 2 | V | $V_{DS}=V_{GS}$, $I_D=250\text{ }\mu\text{A}$ |
| Zero gate voltage drain current | I_{DSS} | - | 0.1 10 | 1 100 | μA | $V_{DS}=40\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ }^\circ\text{C}$ $V_{DS}=40\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ }^\circ\text{C}$ |
| Gate-source leakage current | I_{GSS} | - | 10 | 100 | nA | $V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$ |
| Drain-source on-state resistance | $R_{DS(on)}$ | - | 2.7 3.4 | 3.4 4.6 | $\text{m}\Omega$ | $V_{GS}=10\text{ V}$, $I_D=20\text{ A}$ $V_{GS}=4.5\text{ V}$, $I_D=20\text{ A}$ |
| Gate resistance ¹⁾ | R_G | - | 0.8 | 1.6 | Ω | - |
| Transconductance | g_{fs} | 46 | 93 | - | S | $ V_{DS} >2 I_D R_{DS(on)max}$, $I_D=20\text{ A}$ |

Table 5 Dynamic characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|--------------|--------|------|------|------|--|
| | | Min. | Typ. | Max. | | |
| Input capacitance ¹⁾ | C_{iss} | - | 1800 | 2520 | pF | $V_{GS}=0\text{ V}$, $V_{DS}=20\text{ V}$, $f=1\text{ MHz}$ |
| Output capacitance ¹⁾ | C_{oss} | - | 500 | 700 | pF | $V_{GS}=0\text{ V}$, $V_{DS}=20\text{ V}$, $f=1\text{ MHz}$ |
| Reverse transfer capacitance ¹⁾ | C_{rss} | - | 40 | 80 | pF | $V_{GS}=0\text{ V}$, $V_{DS}=20\text{ V}$, $f=1\text{ MHz}$ |
| Turn-on delay time | $t_{d(on)}$ | - | 4 | - | ns | $V_{DD}=20\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=20\text{ A}$, $R_{G,ext,ext}=1.6\text{ }\Omega$ |
| Rise time | t_r | - | 4 | - | ns | $V_{DD}=20\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=20\text{ A}$, $R_{G,ext,ext}=1.6\text{ }\Omega$ |
| Turn-off delay time | $t_{d(off)}$ | - | 19 | - | ns | $V_{DD}=20\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=20\text{ A}$, $R_{G,ext,ext}=1.6\text{ }\Omega$ |
| Fall time | t_f | - | 3 | - | ns | $V_{DD}=20\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=20\text{ A}$, $R_{G,ext,ext}=1.6\text{ }\Omega$ |

Table 6 Gate charge characteristics²⁾

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|------------------------------------|---------------|--------|------|------|------|--|
| | | Min. | Typ. | Max. | | |
| Gate to source charge | Q_{gs} | - | 4.3 | - | nC | $V_{DD}=20\text{ V}$, $I_D=20\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate charge at threshold | $Q_{g(th)}$ | - | 2.8 | - | nC | $V_{DD}=20\text{ V}$, $I_D=20\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate to drain charge ¹⁾ | Q_{gd} | - | 4.0 | 5.6 | nC | $V_{DD}=20\text{ V}$, $I_D=20\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$ |
| Switching charge | Q_{sw} | - | 5.5 | - | nC | $V_{DD}=20\text{ V}$, $I_D=20\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate charge total ¹⁾ | Q_g | - | 25 | 35 | nC | $V_{DD}=20\text{ V}$, $I_D=20\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate plateau voltage | $V_{plateau}$ | - | 2.5 | - | V | $V_{DD}=20\text{ V}$, $I_D=20\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate charge total ¹⁾ | Q_g | - | 13 | 18 | nC | $V_{DD}=20\text{ V}$, $I_D=20\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$ |
| Gate charge total, sync. FET | $Q_{g(sync)}$ | - | 10 | - | nC | $V_{DS}=0.1\text{ V}$, $V_{GS}=0\text{ to }4.5\text{ V}$ |
| Output charge ¹⁾ | Q_{oss} | - | 22 | 31 | nC | $V_{DD}=20\text{ V}$, $V_{GS}=0\text{ V}$ |

¹⁾ Defined by design. Not subject to production test

²⁾ See "Gate charge waveforms" for parameter definition

Table 7 Reverse diode

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|-------------------------------------|---------------|--------|------|------|------|--|
| | | Min. | Typ. | Max. | | |
| Diode continuous forward current | I_S | - | - | 40 | A | $T_C=25\text{ °C}$ |
| Diode pulse current | $I_{S,pulse}$ | - | - | 160 | A | $T_C=25\text{ °C}$ |
| Diode forward voltage | V_{SD} | - | 0.82 | 1 | V | $V_{GS}=0\text{ V}, I_F=20\text{ A}, T_j=25\text{ °C}$ |
| Reverse recovery time ¹⁾ | t_{rr} | - | 23 | 46 | ns | $V_R=20\text{ V}, I_F=20\text{ A}, di_F/dt=400\text{ A}/\mu\text{s}$ |
| Reverse recovery charge | Q_{rr} | - | 52 | - | nC | $V_R=20\text{ V}, I_F=20\text{ A}, di_F/dt=400\text{ A}/\mu\text{s}$ |

¹⁾ Defined by design. Not subject to production test

4 Electrical characteristics diagrams

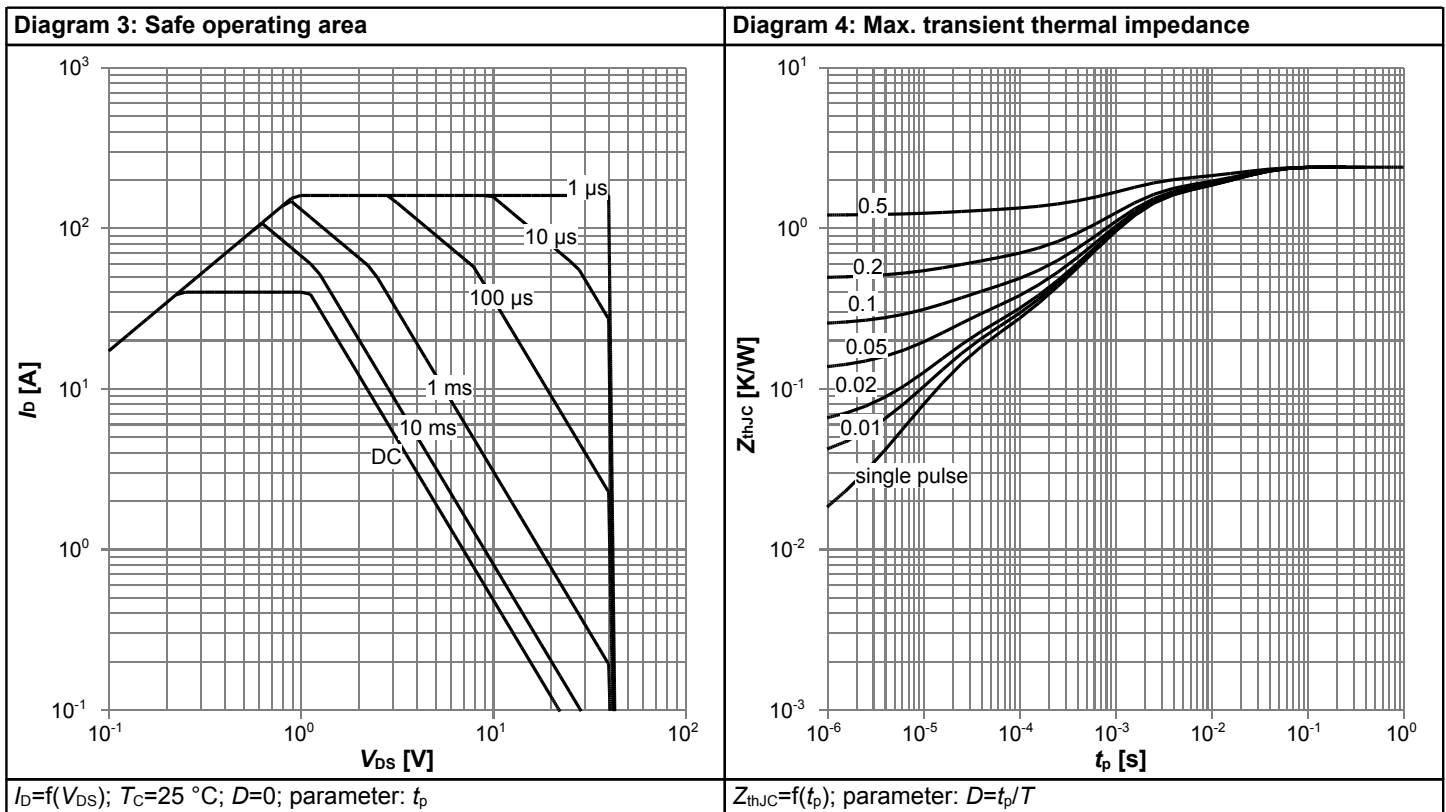
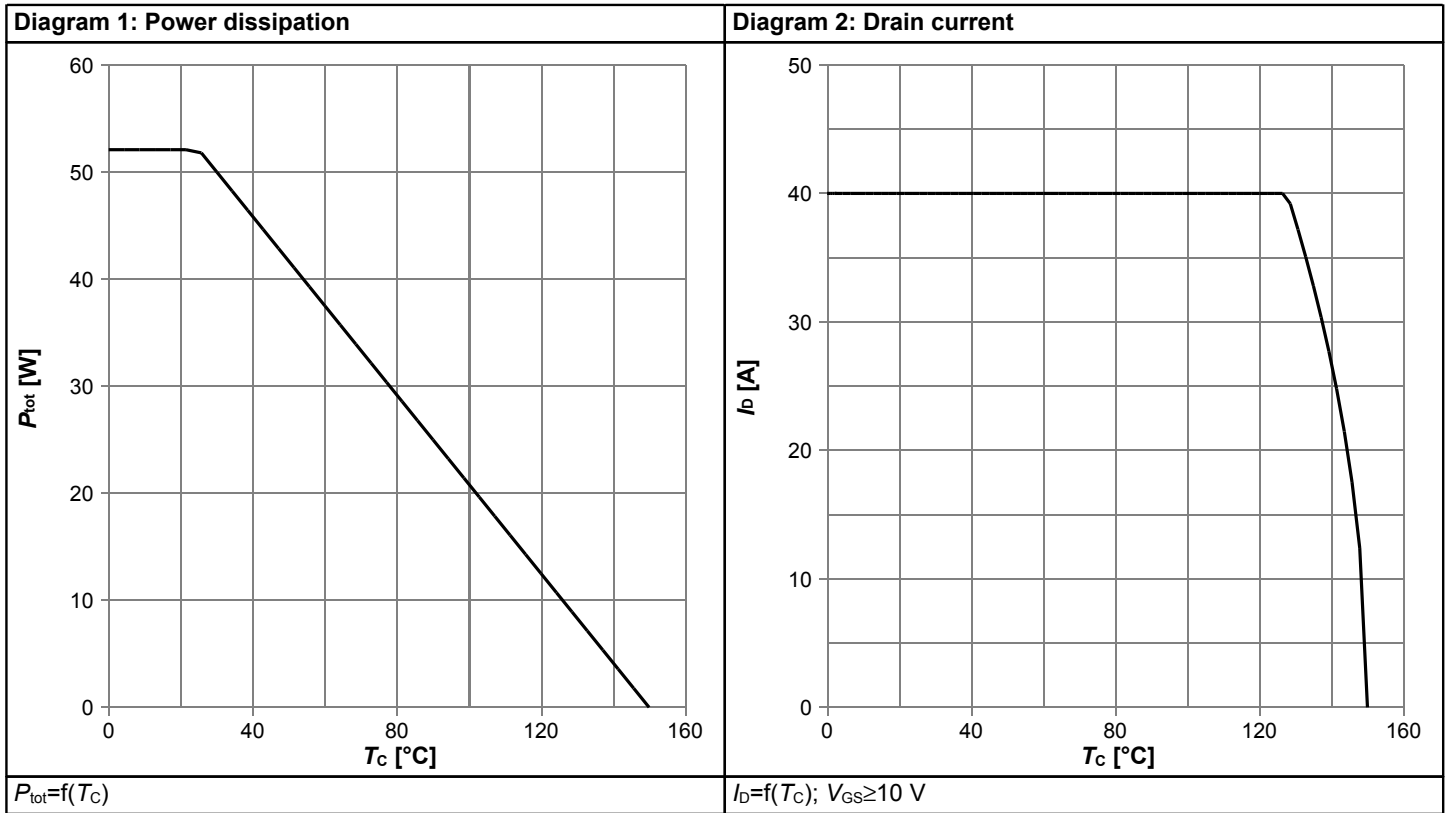
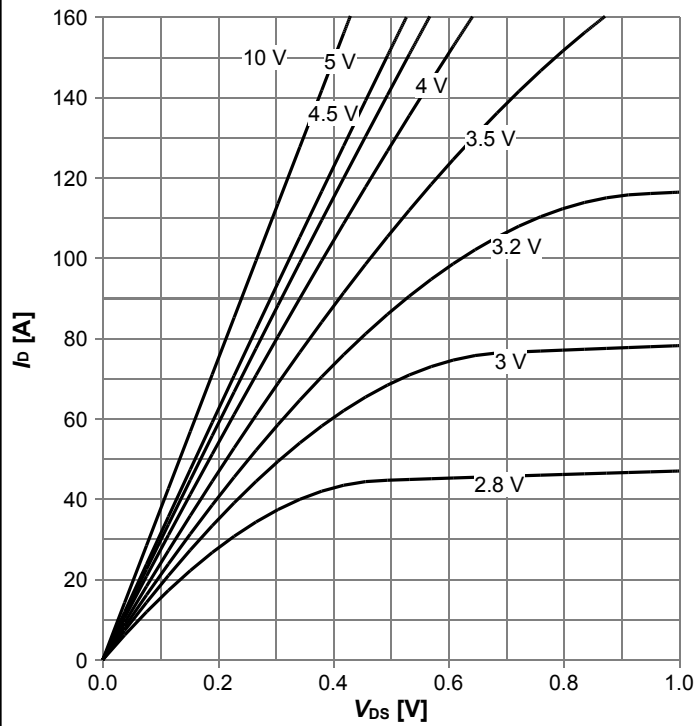
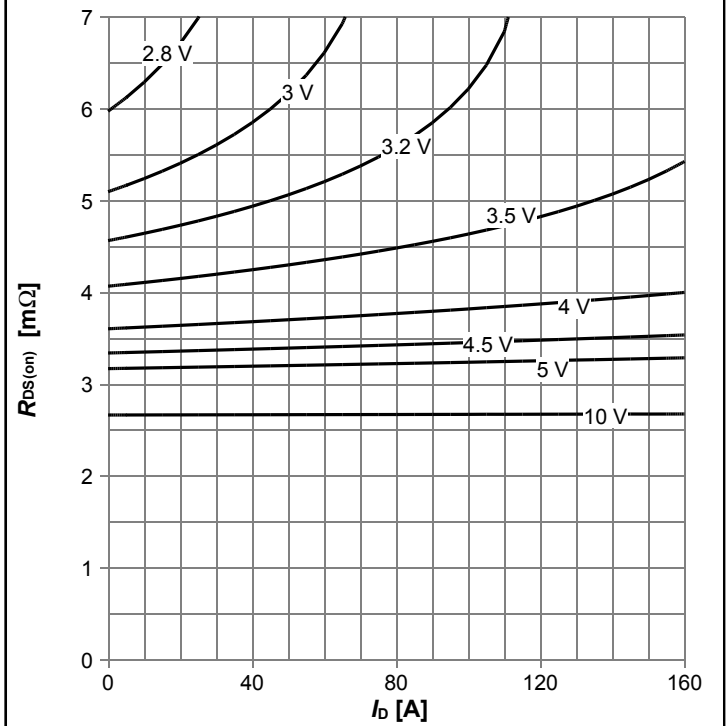


Diagram 5: Typ. output characteristics



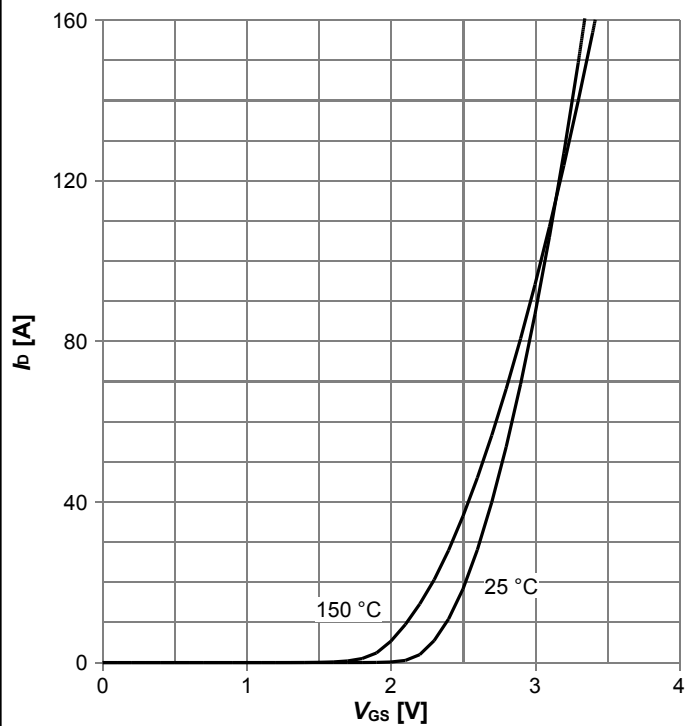
$I_D = f(V_{DS})$; $T_j = 25\text{ °C}$; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



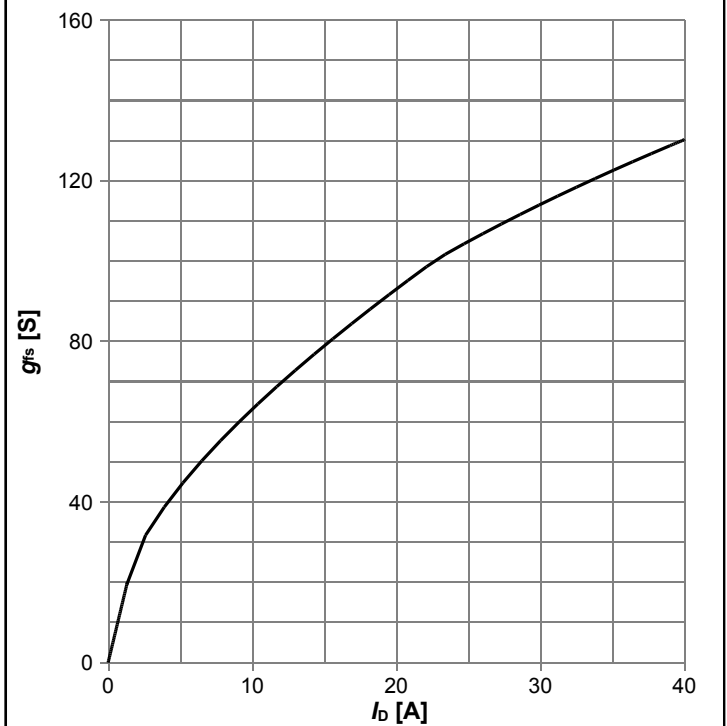
$R_{DS(on)} = f(I_D)$; $T_j = 25\text{ °C}$; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



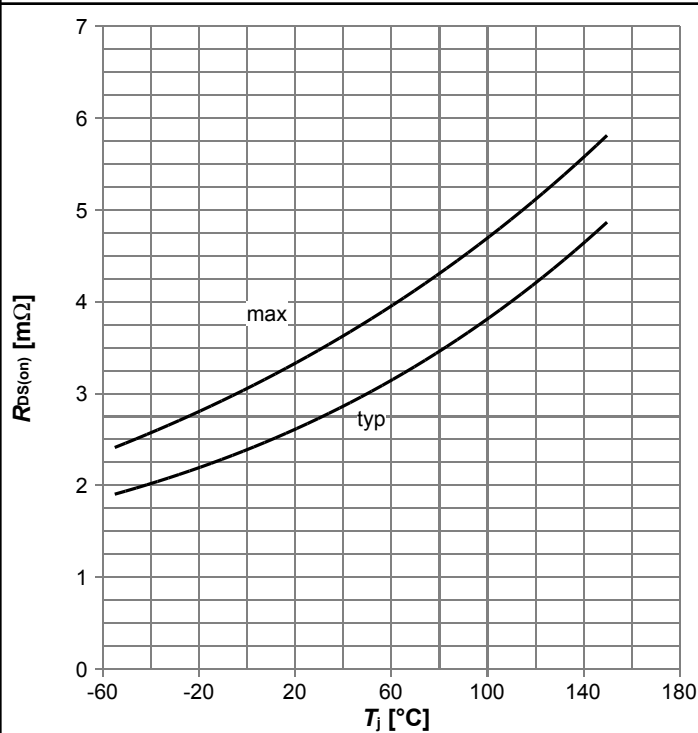
$I_D = f(V_{GS})$; $|V_{DS}| > 2|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. forward transconductance



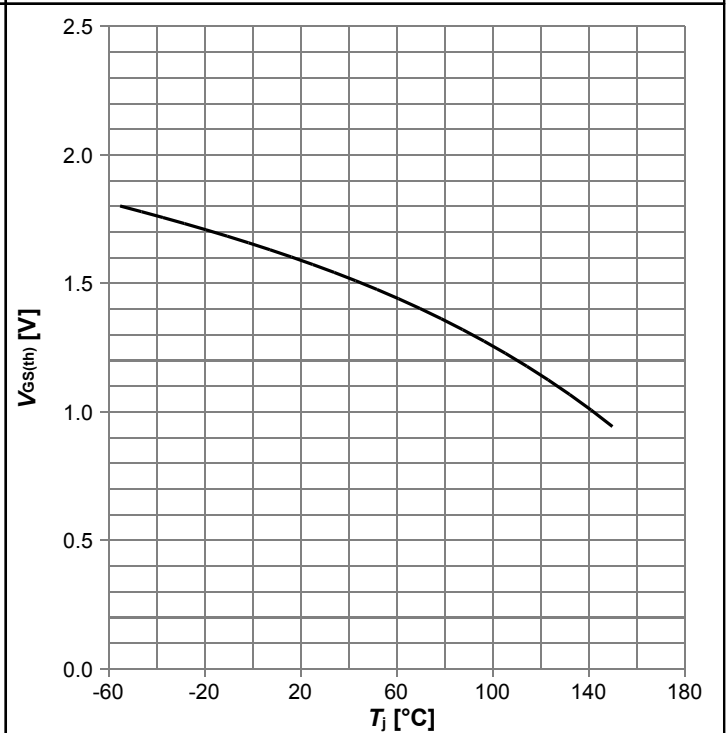
$g_{fs} = f(I_D)$; $T_j = 25\text{ °C}$

Diagram 9: Drain-source on-state resistance



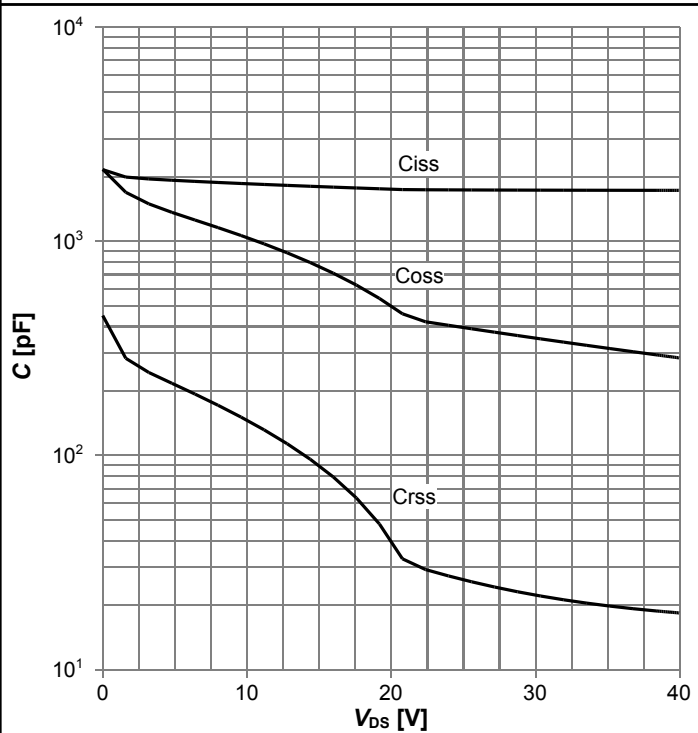
$R_{DS(on)}=f(T_j)$; $I_D=20\text{ A}$; $V_{GS}=10\text{ V}$

Diagram 10: Typ. gate threshold voltage



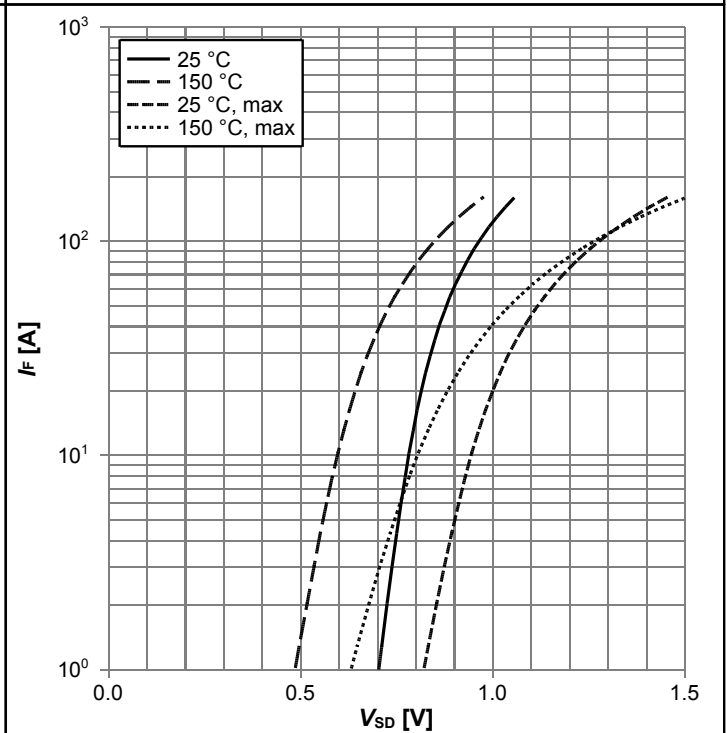
$V_{GS(th)}=f(T_j)$; $V_{GS}=V_{DS}$; $I_D=250\text{ }\mu\text{A}$

Diagram 11: Typ. capacitances



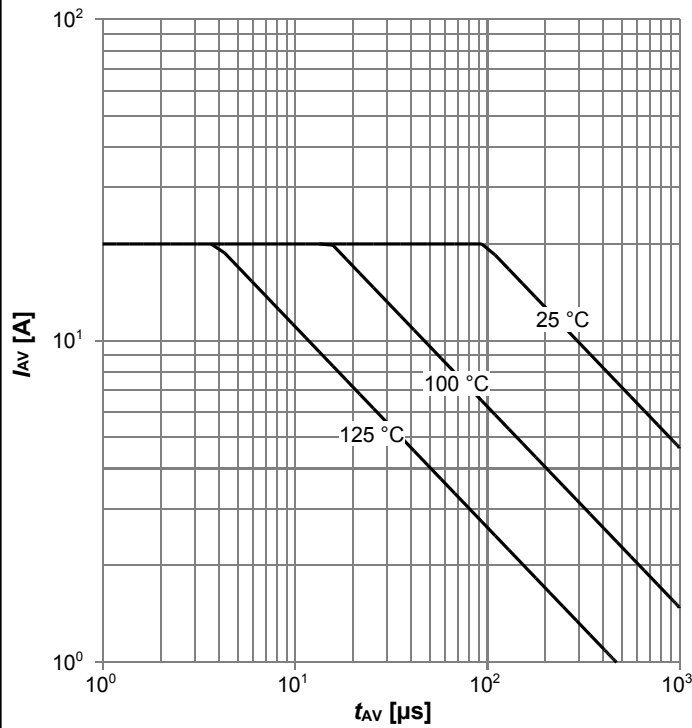
$C=f(V_{DS})$; $V_{GS}=0\text{ V}$; $f=1\text{ MHz}$

Diagram 12: Forward characteristics of reverse diode



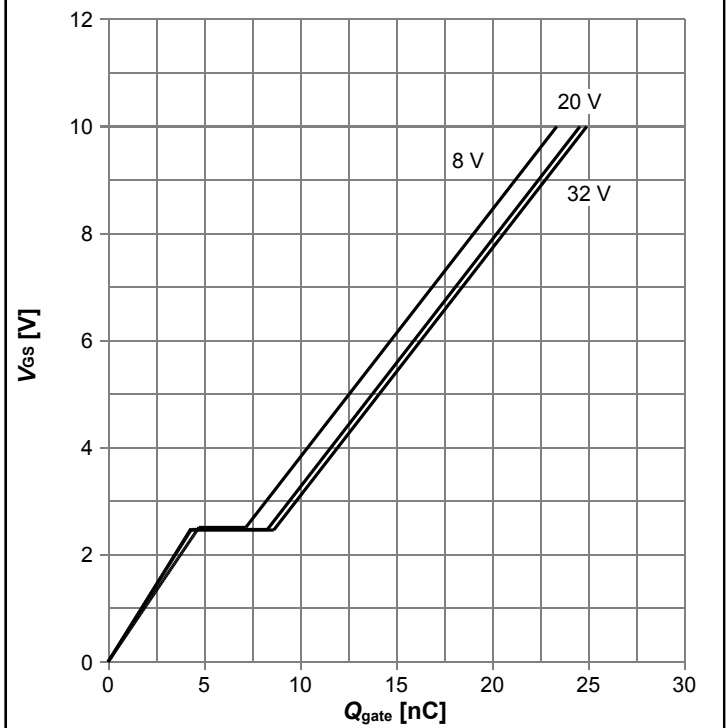
$I_F=f(V_{SD})$; parameter: T_j

Diagram 13: Avalanche characteristics



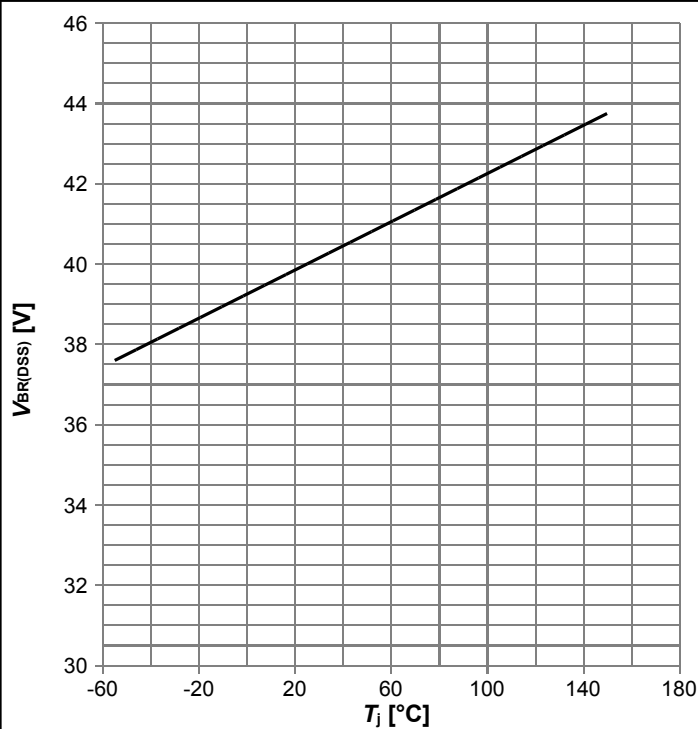
$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$; parameter: $T_{j(start)}$

Diagram 14: Typ. gate charge



$V_{GS}=f(Q_{gate}); I_D=20$ A pulsed; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage



$V_{BR(DSS)}=f(T_j); I_D=1$ mA

Gate charge waveforms



5 Package Outlines



Figure 1 Outline PG-TSDSON-8 FL, dimensions in mm/inches

Revision History

BSZ034N04LS

Revision: 2016-06-09, Rev. 2.1

Previous Revision

| Revision | Date | Subjects (major changes since last revision) |
|----------|------------|--|
| 2.1 | 2016-06-09 | Insert max values and update footnotes |

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